Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method for etching a feature in an integrated circuit wafer incorporating at least one layer of organosilicate glass dielectric over an etch stop layer, the method comprising:

positioning the wafer in a reaction chamber;

introducing a flow of etchant gas mixture including C4F8, CH2F2, oxygen, and CF4 into the reaction chamber;

striking a plasma with the etchant gas in the reaction chamber; and

selectively etching the at least one layer of organosilicate glass with the plasma from the etchant gas with respect to the etch stop layer.

2. (Canceled).

3. (Canceled).

4. (Previously Presented) The method, as recited in claim 1, wherein the etchant gas mixture further comprises argon.

5. (Previously Presented) The method, as recited in claim 4, wherein the at least one layer of organosilicate glass is a first layer of organosilicate glass dielectric, which is etched with the plasma from the etchant gas comprising C4F8, CF4, CH2F2, oxygen and argon.

6. (Original) The method, as recited in claim 5, further comprising stopping the flow of CH2F2 and C4F8 in the etchant gas and using the resulting plasma to etch through an etch stop layer.

7. (Currently Amended) A method for etching a feature in ~~an integrated circuit wafer~~ a first layer of organosilicate glass layer over a silicon carbide etch stop layer, the method comprising:

positioning the wafer in a reaction chamber;

selectively etching through ~~a~~ the first layer of organosilicate glass dielectric with respect to the silicon carbide etch stop layer, comprising:

providing a flow of an etchant gas mixture including C4F8, CH2F2, oxygen, and CF4 into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

8. (Canceled).

9. (Canceled).

10. (Previously Presented) The method, as recited in claim 7, wherein the etchant gas mixture for etching through the first layer of organosilicate glass, further comprises argon.

11. (Currently Amended) The method, as recited in claim 10, further comprising etching through ~~an~~ the silicon carbide etch stop layer, comprising:

providing an etchant gas mixture without C4F8 and CH2F2 into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

12. (Previously Presented) The method, as recited in claim 10, further comprising etching through an etch stop layer after etching through the first layer of organosilicate glass, comprising:

stopping the flow of C4F8 and CH2F2 into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

13. (Previously Presented) The method, as recited in claim 12, further comprising etching through a second layer of organosilicate glass dielectric, comprising:

restarting the flow of C4F8 and CH2F2 into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

14. (Currently Amended) The method, as recited in claim 13, further comprising stripping a photoresist mask above the layer of organosilicate glass, wherein the photoresist mask is used to pattern the layer of organosilicate glass, comprising:

stopping the flow of C4F8 and CF4 into the reaction chamber, after etching through the second layer of organosilicate glass;

providing a flow of nitrogen into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

15. (Withdrawn) An integrated circuit formed by the method comprising:

positioning a wafer in a reaction chamber;

etching through a first layer of organosilicate glass dielectric over the wafer, comprising:

providing a flow of an etchant gas mixture including C4F8 and CF4 into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

16. (Withdrawn) The integrated circuit, as recited in claim 15, wherein the etchant gas mixture for etching through the first layer of organosilicate glass, further comprises CH2F2, oxygen, and argon.

17. (Withdrawn) The integrated circuit, as recited in claim 16, wherein the method further comprises etching through an etch stop layer, comprising:

providing an etchant gas mixture without C4F8 and CF4 into the reaction chamber; and

generating a plasma with the etchant gas in the reaction chamber.

18. (Withdrawn) The integrated circuit, as recited in claim 16, wherein the method further comprises etching through an etch stop layer after etching through the first layer of organosilicate glass, comprising:

stopping the flow of C4F8 and CF4 into the reaction chamber; and

generating a plasma with the resulting etchant gas in the reaction chamber.

19. (Canceled).

20. (Currently Amended) The method, as recited in claim 12, further comprising stripping a photoresist mask above the layer of organosilicate glass, wherein the photoresist mask is used to pattern the layer of organosilicate glass, comprising:

stopping the flow of C4F8 and CF4 into the reaction chamber, after etching through the etch stop layer;

providing a flow of nitrogen into the reaction chamber; and

generating a plasma in the reaction chamber.

21. (Currently Amended) The method, as recited in claim 6, further comprising stripping a photoresist mask above the layer of organosilicate glass, wherein the photoresist mask is used to pattern the layer of organosilicate glass, comprising:

stopping the flow of C4F8 and CF4 into the reaction chamber, after etching through the etch stop layer;

providing a flow of nitrogen into the reaction chamber; and

generating a plasma in the reaction chamber.